

L Number	Hits	Search Text	DB	Time stamp
1	112	((testing or test or measuring or measures or measured) with (electrical near3 characteristic) and (address with bit))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 11:17
2	11	((testing or test or measuring or measures or measured) with (electrical near3 characteristic) and (address with bit)) and packaged and pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 11:13
3	5	((testing or test or measuring or measures or measured) with (electrical near3 characteristic) and (address with bit)) and nmos and pmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 11:22
4	8275	(testing or measuring) with (transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 11:24
5	2025	((testing or measuring) with (transistor)) and ((testing or measuring with (resistor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 11:25
6	2025	((testing or measuring) with (transistor)) and (((testing or measuring) with (transistor)) and ((testing or measuring) with (resistor)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 11:25
7	12	(((testing or measuring) with (transistor)) and (((testing or measuring) with (transistor)) and ((testing or measuring) with (resistor)))) and (address adj3 bit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 11:37
8	56	(semiconductor with (packaged adj2 state))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 11:39
9	35	((semiconductor with (packaged adj2 state))) and (test or testing or measuring or measure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/17 11:40